

Description

The HSS3402A is the high cell density trenched N-ch MOSFETs, which provides excellent R_{DS(ON)} and efficiency for most of the small power switching and load switch applications.

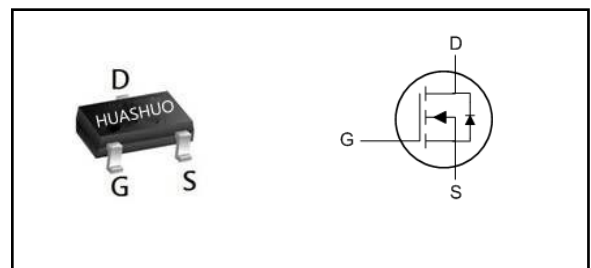
The HSS3402A meet the RoHS and Green Product requirement with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- Excellent C_{dv/dt} effect decline
- Advanced high cell density Trench technology

Product Summary

| | | |
|-------------------------|-----|----|
| V _{DS} | 30 | V |
| R _{DS(ON),max} | 28 | mΩ |
| I _D | 5.3 | A |

SOT23 Pin Configuration



Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|--------------------------------------|---|------------|-------|
| V _{DS} | Drain-Source Voltage | 30 | V |
| V _{GS} | Gate-Source Voltage | ± 12 | V |
| I _D @T _A =25°C | Continuous Drain Current, V _{GS} @ 4.5V ₁ | 5.3 | A |
| I _D @T _A =70°C | Continuous Drain Current, V _{GS} @ 4.5V ₁ | 4.5 | A |
| I _{DM} | Pulsed Drain Current ₂ | 22 | A |
| P _D @T _A =25°C | Total Power Dissipation ₃ | 1.0 | W |
| T _{STG} | Storage Temperature Range | -55 to 150 | °C |
| T _J | Operating Junction Temperature Range | -55 to 150 | °C |

Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|------------------|--|------|------|------|
| R _{θJA} | Thermal Resistance Junction-ambient ₁ | --- | 100 | °C/W |
| R _{θJC} | Thermal Resistance Junction-Case ₁ | --- | 80 | °C/W |



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------------|--|---|------|-------|------|-------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250uA | 30 | --- | --- | V |
| ΔBV _{DSS} /ΔT _J | BVDSS Temperature Coefficient | Reference to 25°C, I _D =1mA | --- | 0.029 | --- | V/°C |
| R _{DS(ON)} | Static Drain-Source On-Resistance ² | V _{GS} =10V, I _D =5.9A | --- | 19 | 28 | mΩ |
| | | V _{GS} =4.5V, I _D =5A | --- | 23 | 31 | |
| | | V _{GS} =2.5V, I _D =4A | --- | 38 | 48 | |
| V _{GS(th)} | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =250uA | 0.7 | 0.9 | 1.4 | V |
| ΔV _{GS(th)} | V _{GS(th)} Temperature Coefficient | | --- | -2.82 | --- | mV/°C |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =24V, V _{GS} =0V, T _J =25°C | --- | --- | 1 | uA |
| | | V _{DS} =24V, V _{GS} =0V, T _J =55°C | --- | --- | 5 | |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±12V, V _{DS} =0V | --- | --- | ±100 | nA |
| g _{fs} | Forward Transconductance | V _{DS} =5V, I _D =3A | --- | 19 | --- | S |
| R _g | Gate Resistance | V _{DS} =0V, V _{GS} =0V, f=1MHz | --- | 1.5 | 3 | Ω |
| Q _g | Total Gate Charge (4.5V) | V _{DS} =15V, V _{GS} =4.5V, I _D =3A | --- | 3.74 | --- | nC |
| Q _{gs} | Gate-Source Charge | | --- | 0.62 | --- | |
| Q _{gd} | Gate-Drain Charge | | --- | 1.82 | --- | |
| T _{d(on)} | Turn-On Delay Time | V _{DD} =15V, V _{GS} =4.5V, R _G =3.3Ω I _D =3A | --- | 6.5 | --- | ns |
| T _r | Rise Time | | --- | 2 | --- | |
| T _{d(off)} | Turn-Off Delay Time | | --- | 28.6 | --- | |
| T _f | Fall Time | | --- | 2.6 | --- | |
| C _{iss} | Input Capacitance | V _{DS} =15V, V _{GS} =0V, f=1MHz | --- | 614 | --- | pF |
| C _{oss} | Output Capacitance | | --- | 78 | --- | |
| C _{rss} | Reverse Transfer Capacitance | | --- | 61 | --- | |

Diode Characteristics

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-----------------|--|---|------|------|------|------|
| I _S | Continuous Source Current ^{1,4} | V _G =V _D =0V, Force Current | --- | --- | 5.5 | A |
| I _{SM} | Pulsed Source Current ^{2,4} | | --- | --- | 22 | A |
| V _{SD} | Diode Forward Voltage ² | V _{GS} =0V, I _S =1A, T _J =25°C | --- | --- | 1.2 | V |
| t _{rr} | Reverse Recovery Time | I _F =3A, dI/dt=100A/μs, T _J =25°C | --- | 6.8 | --- | nS |
| Q _{rr} | Reverse Recovery Charge | | --- | 2.3 | --- | nC |

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

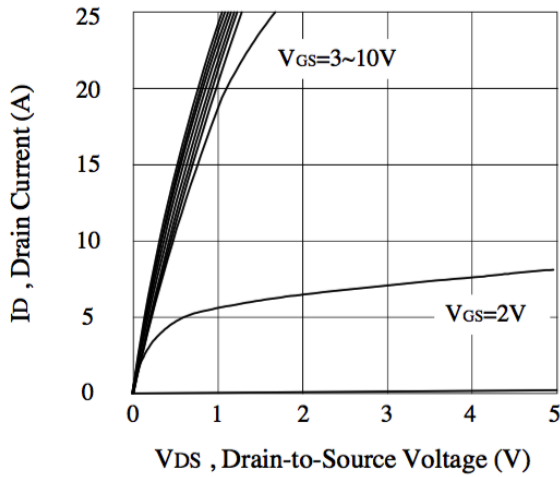


Figure 1. Output Characteristics

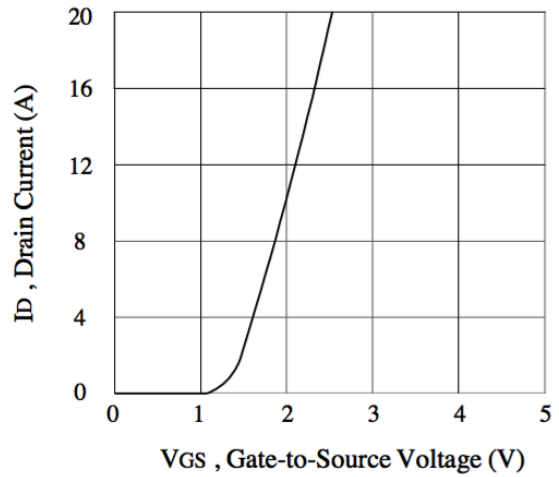


Figure 2. Transfer Characteristics

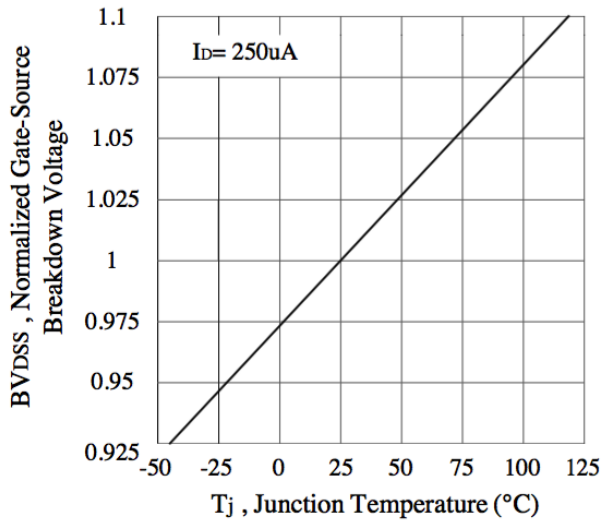


Figure 3. Breakdown Voltage Variation with Temperature

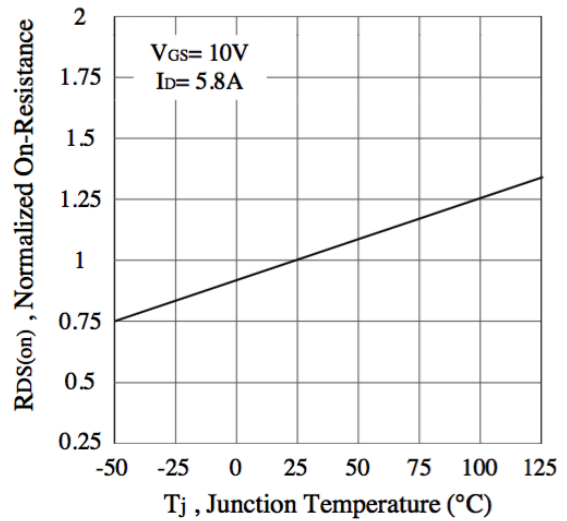


Figure 4. On-Resistance Variation with Temperature

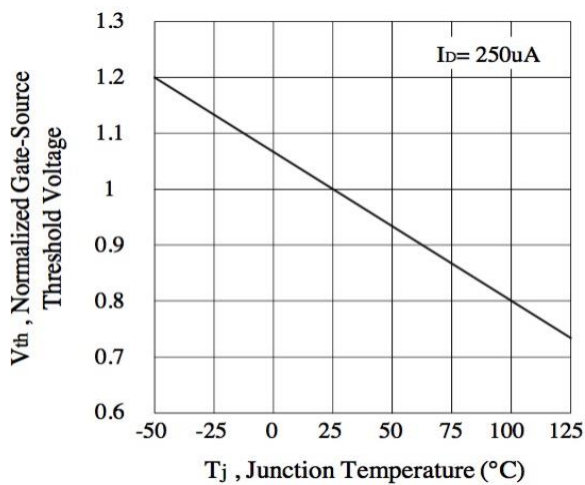


Figure 5. Gate Threshold Variation with Temperature

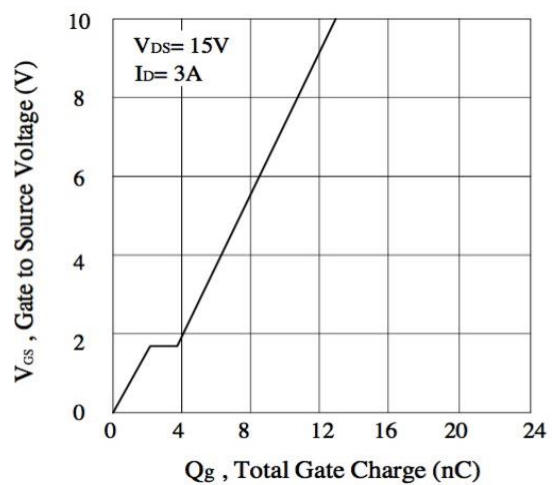


Figure 6. Gate Charge

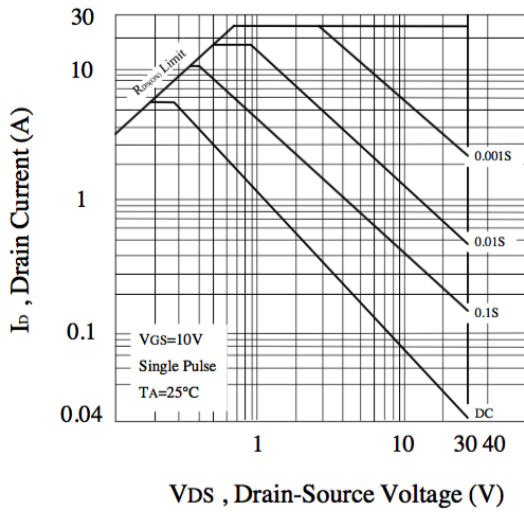


Figure 7. Maximum Safe Operating Area

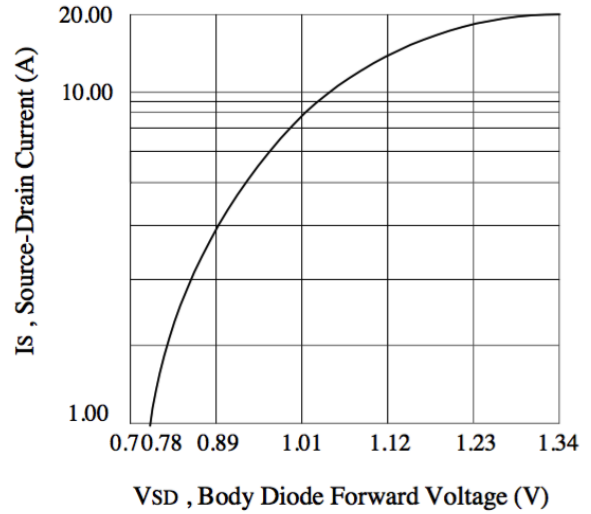


Figure 8. Body Diode Forward Voltage Variation with Source Current

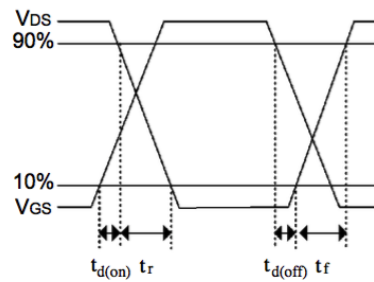
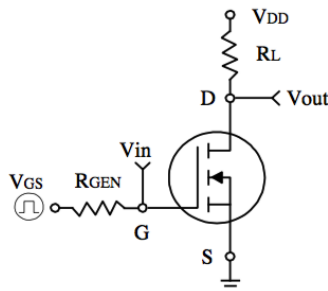


Figure 9. Switching Test Circuit and Switching Waveforms

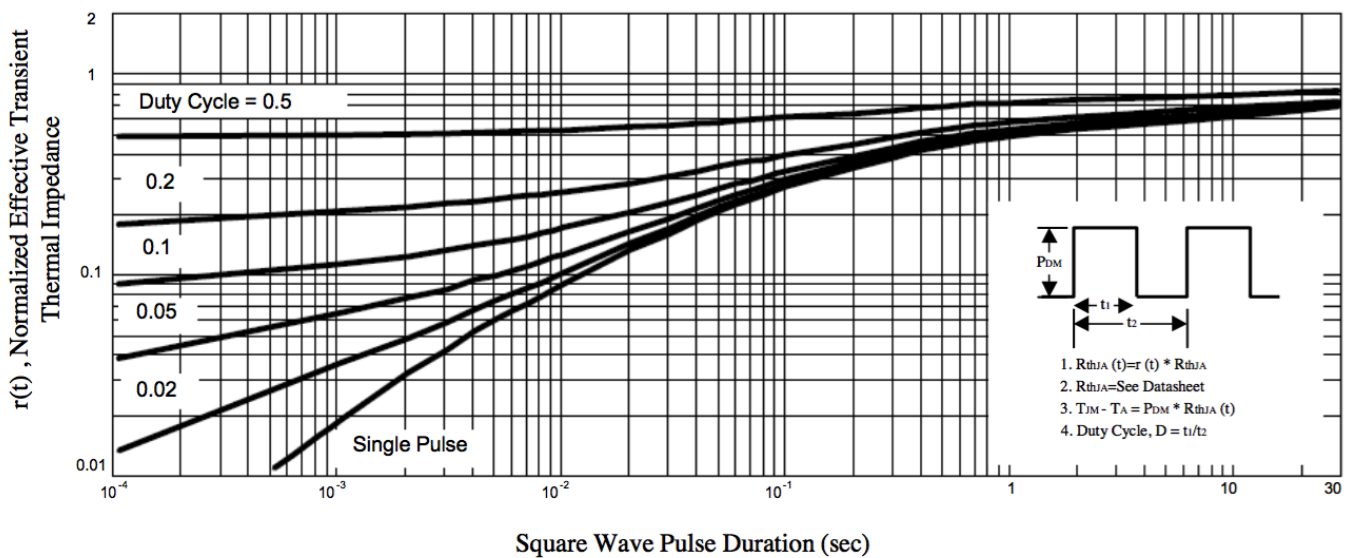
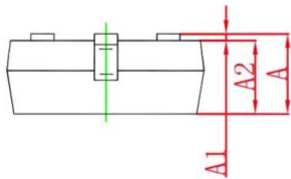
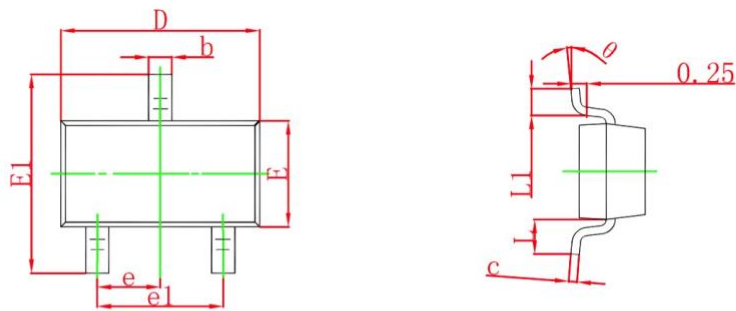


Figure 10. Normalized Thermal Transient Impedance Curve



Ordering Information

| Part Number | Package code | Packaging |
|-------------|--------------|----------------|
| HSS3402A | SOT-23 | 3000/Tape&Reel |



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.047 | 0.055 |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 |
| e | 0.950 TYP | | 0.037 TYP | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.550 REF | | 0.022 REF | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| θ | 0° | 8° | 0° | 8° |

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